

# HIGH SPEED 2K x 8 DUAL PORT STATIC RAM **HIGH SPEED** STATIC RAM



### Features

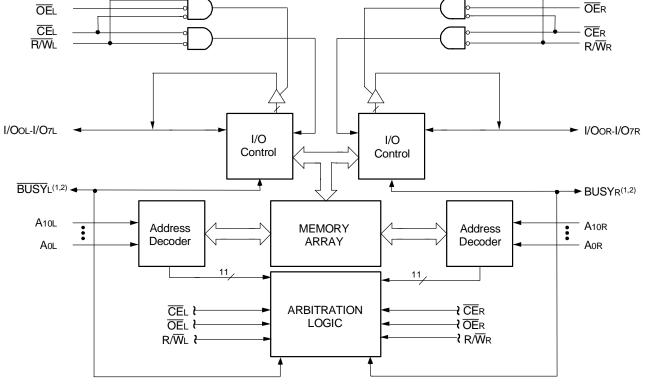
- High-speed access
  - Commercial: 20/25/35/55/100ns (max.)

**Functional Block Diagram** 

- Industrial: 25ns (max.)
- Military: 25/35/55/100ns (max.)
- ٠ Low-power operation
  - IDT7132/42SA
    - Active: 325mW (typ.)
  - Standby: 5mW (typ.)
  - IDT7132/42LA

  - Active: 325mW (typ.) Standby: 1mW (typ.)

- ٠ MASTER IDT7132 easily expands data bus width to 16-or-more bits using SLAVE IDT7142
- ٠ On-chip port arbitration logic (IDT7132 only)
- BUSY output flag on IDT7132; BUSY input on IDT7142 ٠
- Battery backup operation —2V data retention (LA only)
- TTL-compatible, single 5V ±10% power supply
- ٠ Available in 48-pin DIP, LCC and Flatpack, and 52-pin PLCC packages
- ٠ Military product compliant to MIL-PRF-38535 QML
- ٠ Industrial temperature range (-40°C to +85°C) is available for selected speeds
- OEL CEL R/WL



2692 drw 01

- 1. IDT7132 (MASTER):  $\overline{\text{BUSY}}$  is open drain output and requires pullup resistor of 270 $\Omega$ . IDT7142 (SLAVE): BUSY is input.
- 2. Open drain output: requires pullup resistor of 270Ω.

### Description

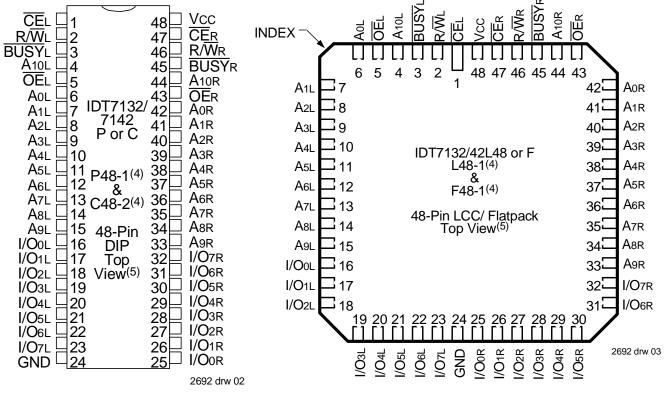
The IDT7132/IDT7142 are high-speed 2K x 8 Dual-Port Static RAMs. The IDT7132 is designed to be used as a stand-alone 8-bit Dual-Port RAM or as a "MASTER" Dual-Port RAM together with the IDT7142 "SLAVE" Dual-Port in 16-bit-or-more word width systems. Using the IDT MASTER/ SLAVE Dual-Port RAM approach in 16-or-more-bit memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by CE permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 325mW of power. Low-power (LA) versions offer battery backup data retention capability, with each Dual-Port typically consuming 200µW from a 2V battery.

The IDT7132/7142 devices are packaged in a 48-pin sidebraze or plastic DIPs, 48-pin LCCs, 52-pin PLCCs, and 48-lead flatpacks. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

### **Pin Configurations**<sup>(1,2,3)</sup>



#### NOTES:

- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- P48-1 package body is approximately .55 in x 2.43 in x .18 in. C48-2 package body is approximately .62 in x 2.43 in x .15 in. L48-1 package body is approximately .57 in x .57 in x .68 in. F48-1 package body is approximately .75 in x .75 in x .11 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

# **Capacitance**<sup>(1)</sup> (TA = +25°C,f = 1.0MHz)

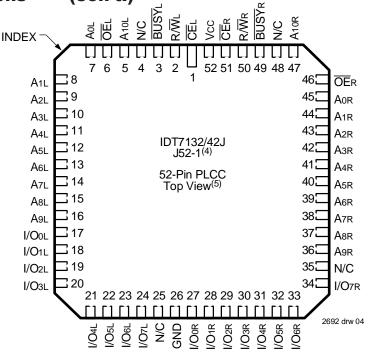
Symbol	Parameter	Conditions <sup>(2)</sup>	Max.	Unit
Cin	Input Capacitance	ViN = 3dV	11	рF
Соит	Output Capacitance	Vout = 3dV	11	pF
				2692 thi 00

NOTES:

1. This parameter is determined by device characterization but is not production tested.

3dV represents the interpolated capacitance when the input and output signals switch from 3V to 0V.

# **Pin Configurations**<sup>(1,2,3)</sup> (con't.)



#### NOTES:

1. All Vcc pins must be connected to the power supply.

2. All GND pins must be connected to the ground supply.

3. Package body is approximately .75 in x .75 in x .17 in.

4. This package code is used to reference the package diagram.

5. This text does not indicate orientation of the actual part-marking.

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
TSTG	Storage Temperature	-65 to +150	-65 to +150	°C
Ιουτ	DC Output Current	50	50	mA

### Absolute Maximum Ratings<sup>(1)</sup>

#### NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of the specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

 VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

### **Recommended Operating Temperature and Supply Voltage**<sup>(1,2)</sup>

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

2692 tbl 01

2692 tbl 02

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1. This is the parameter TA. This is the "instant on" case temperature.

Industrial temperature: for specific speeds, packages and powers contact your sales office.

### **Recommended DC Operating Conditions**

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
VIH	Input High Voltage	2.2	—	6.0 <sup>(2)</sup>	V
VIL	Input Low Voltage	-0.5(1)		0.8	V

NOTES:

1. VIL (min.) = -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,5,8)</sup> (Vcc = 5.0V ± 10%)

					7142	X20 <sup>(2)</sup> X20 <sup>(2)</sup> Only	7142 Com	X25 <sup>(7)</sup> X25 <sup>(7)</sup> 'I, Ind litary	714: Con	2X35 2X35 1'I & tary	
Symbol	Parameter	Test Condition	Versi	on	Тур.	Max.	Тур.	Max.	Тур.	Max.	Unit
ICC	Dynamic Operating Current (Both Ports Active)	CEL = CER = VIL, Outputs Disabled f = fMaX <sup>(3)</sup>	COM'L	SA LA	110 110	250 200	110 110	220 170	80 80	165 120	mA
		t = TMAX <sup>(0)</sup>	MIL & IND	SA LA			110 110	280 220	80 80	230 170	
ISB1	Standby Current (Both Ports - TTL Level Inputs)	$\overline{CEL} = \overline{CER} = VIH,$ f = fMAX <sup>(3)</sup>	COM'L	SA LA	30 30	65 45	30 30	65 45	25 25	65 45	mA
	Level liipus)		MIL & IND	SA LA			30 30	80 60	25 25	80 60	
ISB2	Standby Current (One Port - TTL	CE"A" = VIL and CE"B" = VIH <sup>(6)</sup> Active Port Outputs Disabled	COM'L	SA LA	65 65	165 125	65 65	150 115	50 50	125 90	mA
	Level Inputs)	f=fMAX <sup>(3)</sup>	MIL & IND	SA LA			65 65	160 125	50 50	150 115	
ISB3	Full Standby Current (Both Ports - All	$\overline{\text{CEL}}$ and $\overline{\text{CER}} \geq \text{Vcc}$ -0.2V VIN $\geq$ Vcc -0.2V or VIN $\leq$ 0.2V, f = 0 <sup>(4)</sup>	COM'L	SA LA	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 4	mA
	CMOS Level Inputs)		MIL & IND	SA LA			1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\overline{CE}^{"}A^{"} \leq 0.2V \text{ and } \overline{CE}^{"}B^{"} \geq Vcc - 0.2V^{(6)}$ VIN $\geq Vcc - 0.2V \text{ or } VIN \leq 0.2V$	COM'L	SA LA	60 60	155 115	60 60	145 105	45 45	110 85	mA
	Givios Level inputs)	Active Port Outputs Disabled f = fMAX <sup>(3)</sup>	MIL & IND	SA LA			60 60	155 115	45 45	145 105	

					714 Cor	2X55 2X55 n'I & itary	7142 Con	X100 X100 n'l & tary	
Symbol	Parameter	Test Condition	Versie	on	Тур.	Max.	Тур.	Мах.	Unit
lcc	Dynamic Operating Current (Both Ports Active)	CEL = CER = VL, Outputs Disabled f = fMAX <sup>(0)</sup>	COM'L	SA LA	65 65	155 110	65 65	155 110	mA
	(Both Polis Active)	1 - IMAX*'	MIL & IND	SA LA	65 65	190 140	65 65	190 140	
ISB1	Standby Current (Both Ports - TTL	$\overline{CEL} = \overline{CER} = VH,$ f = fMAX <sup>(3)</sup>	COM'L	SA LA	20 20	65 35	20 20	55 35	mA
	Level Inputs)		MIL & IND	SA LA	20 20	65 45	20 20	65 45	
ISB2	Standby Current (One Port - TTL	$\overline{CE}^{*}A^{*} = VL$ and $\overline{CE}^{*}B^{*} = VH^{(6)}$ Active Port Outputs Disabled	COM'L	SA LA	40 40	110 75	40 40	110 75	mA
	Level Inputs)	f=fmax <sup>(3)</sup>	MIL & IND	SA LA	40 40	125 90	40 40	125 90	
ISB3	Full Standby Current (Both Ports - All	$\overline{CE}$ L and $\overline{CER} \ge VCC$ -0.2V VIN $\ge VCC$ -0.2V or VIN $\le 0.2V$ , f = 0 <sup>(4)</sup>	COM'L	SA LA	1.0 0.2	15 4	1.0 0.2	15 4	mA
	CMOS Level Inputs)		MIL & IND	SA LA	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All	CE <sup>*</sup> A <sup>*</sup> ≤ 0.2V and CE <sup>*</sup> B <sup>*</sup> ≥ Vcc -0.2V <sup>(6)</sup> VIN ≥ Vcc - 0.2V or VIN ≤ 0.2V	COM'L	SA LA	40 40	100 70	40 40	95 70	mA
	CMOS Level Inputs)	Active Port Outputs Disabled f = fMAX <sup>0)</sup>	MIL & IND	SA LA	40 40	110 85	40 40	110 80	

2692 tbl 04b

2692 tbl 04a

#### NOTES:

1. 'X' in part numbers indicates power rating (SA or LA).

2. PLCC Package only

- At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC TEST CONDITIONS" of input levels
  of GND to 3V.
- 4. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.
- 5. Vcc = 5V, TA=+25°C for Typ and is not production tested. Vcc DC = 100mA (Typ)
- 6. Port "A" may be either left or right port. Port "B" is opposite from port "A".

7. Not available in DIP packages.

<sup>8.</sup> Industrial temperature: for specific speeds, packages and powers contact your sales office.

### **DC Electrical Characteristics Over the Operating Temperature Supply Voltage Range** (Vcc = 5.0V ± 10%)

				2SA 2SA		2LA 2LA	
Symbol	Parameter	Test Conditions	Min.	Мах.	Min.	Max.	Unit
ILI	Input Leakage Current <sup>(1)</sup>	$V_{CC} = 5.5V,$ $V_{IN} = 0V$ to $V_{CC}$	_	10		5	μA
ILO	Output Leakage Current	$\frac{V_{CC}}{CE}$ = 5.5V, CE = VIH, Vout = 0V to Vcc	—	10	_	5	μA
Vol	Output Low Voltage	Iol = 4mA		0.4	_	0.4	V
Vol	Open Drain O <u>utput</u> Low Voltage (BUSY)	Iol = 16mA	_	0.5	_	0.5	V
Vон	Output High Voltage	Іон = -4mA	2.4	_	2.4		V

NOTE:

1. At Vcc  $\leq$  2.0V leakages are undefined.

### 2692 tbl 05

2692 tb106

### **Data Retention Characteristics (LA Version Only)**

Symbol	Parameter	Test Condition	n	Min.	Typ. <sup>(1)</sup>	Max.	Unit
Vdr	Vcc for Data Retention	Vcc = 2.0V		2.0	_	_	V
ICCDR	Data Retention Current	<u>CE ≥</u> Vcc -0.2V	Mil. & Ind.	_	100	4000	μA
		Vin <u>&gt;</u> Vcc -0.2V or	Com'l.	_	100	1500	μA
tCDR <sup>(3)</sup>	Chip Deselect to Data Retention Time	Vin <u>&lt;</u> 0.2V		0	I		ns
$t R^{(3)}$	Operation Recovery Time			tRC <sup>(2)</sup>	_	_	ns

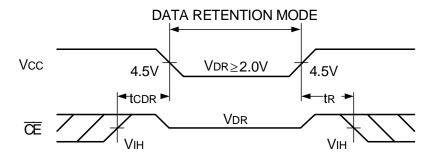
NOTES:

1. Vcc = 2V, TA = +25°C, and is not production tested.

2. tRC = Read Cycle Time

3. This parameter is guaranteed but not production tested.

### **Data Retention Waveform**



2692 drw 05

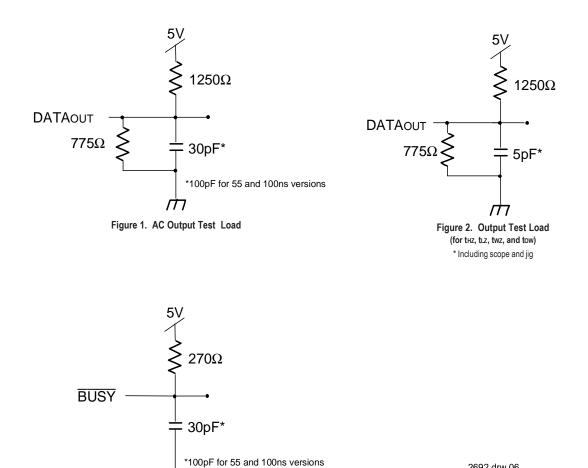
Military, Industrial and Commercial Temperature Ranges

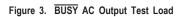
2692 drw 06

### **AC Test Conditions**

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns Max.
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1, 2, and 3

2692 tbl 07





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2692 tbl 08b

### AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(3,5)</sup>

		7142	X20 <sup>(2)</sup> X20 <sup>(2)</sup> I Only	7132X25 <sup>(2)</sup> 7142X25 <sup>(2)</sup> Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYC	CLE							
tRC	Read Cycle Time	20		25		35		ns
tAA	Address Access Time		20		25		35	ns
<b>t</b> ACE	Chip Enable Access Time		20	-	25		35	ns
<b>t</b> AOE	Output Enable Access Time		11		12		20	ns
tон	Output Hold from Address Change	3		3		3	_	ns
ŧz	Output Low-Z Time <sup>(1,4)</sup>	0		0		0		ns
tHZ	Output High-Z Time <sup>(1,4)</sup>	_	10	_	10	_	15	ns
tPU	Chip Enable to Power Up Time <sup>(4)</sup>	0		0		0		ns
tPD	Chip Disable to Power Down Time <sup>(4)</sup>	_	20		25		35	ns
			-		-		26	692 tbl 08a
				714 Cor	2X55 2X55 n'l & itary	7142 Cor	2X100 2X100 n'I & itary	

		Mili	Military		Military	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYC	2LE					
tRC	Read Cycle Time	55		100		ns
tAA	Address Access Time		55		100	ns
tACE	Chip Enable Access Time		55		100	ns
taoe	Output Enable Access Time		25		40	ns
tон	Output Hold from Address Change	3		10	_	ns
tLΖ	Output Low-Z Time <sup>(1,4)</sup>	5		5		ns
tHZ	Output High-Z Time <sup>(1,4)</sup>		25		40	ns
t₽U	Chip Enable to Power Up Time <sup>(4)</sup>	0		0		ns
tPD	Chip Disable to Power Down Time <sup>(4)</sup>		50		50	ns

NOTES:

1. Transition is measured 0mV from Low or High-Impedance Voltage Output Test Load (Figure 2).

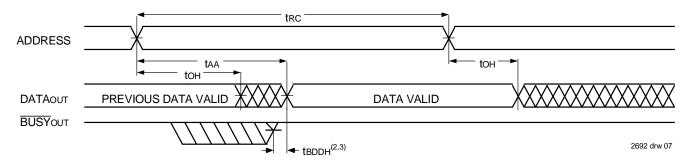
2. PLCC package only.

3. 'X' in part numbers indicates power rating (SA or LA).

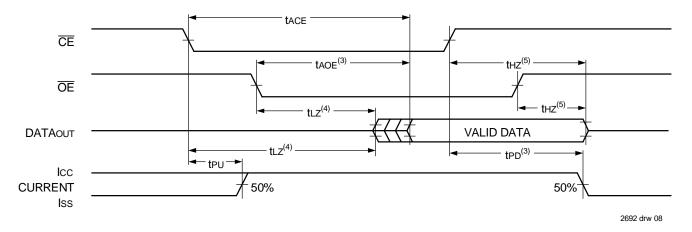
4. This parameter is guaranteed by device characterization, but is not production tested.

5. Industrial temperature: for specific speeds, packages and powers contact your sales office.

# Timing Waveform of Read Cycle No. 1, Either Side<sup>(1)</sup>



# Timing Waveform of Read Cycle No. 2, Either Side<sup>(1)</sup>



- 1.  $R\overline{W} = V_{H}, \overline{CE} = V_{L}$ , and is  $\overline{OE} = V_{L}$ . Address is valid prior to the coincidental with  $\overline{CE}$  transition LOW.
- 2. tBDD delay is required only in the case where the opposite port is completing a write operation to the same address location. For simultaneous read operations, BUSY has no relationship to valid output data.
- 3. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA, and tBDD.
- 4. Timing depends on which signal is asserted last, OE or CE.
- 5. Timing depends on which signal is de-asserted first,  $\overline{\text{OE}}$  or  $\overline{\text{CE}}$ .

### AC Electrical Characteristics Over the Operating Temperature Supply Voltage Range<sup>(5,6)</sup>

		7142	X20 <sup>(2)</sup> X20 <sup>(2)</sup> I Only	7142 Com	X25 <sup>(2)</sup> X25 <sup>(2)</sup> 'I, Ind litary	7142 Con	2X35 2X35 n'I& itary	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCL	E	_		-		-		
twc	Write Cycle Time <sup>(3)</sup>	20		25		35		ns
tew	Chip Enable to End-of-Write	15		20		30		ns
taw	Address Valid to End-of-Write	15		20		30		ns
tas	Address Set-up Time	0		0		0		ns
twp	Write Pulse Width <sup>(4)</sup>	15		15		25		ns
twR	Write Recovery Time	0		0		0		ns
tow	Data Valid to End-of-Write	10		12		15		ns
tHZ	Output High-Z Time <sup>(1)</sup>	-	10		10		15	ns
tDH	Data Hold Time	0		0		0	_	ns
twz	Write Enable to Output in High-Z <sup>(1)</sup>		10		10		15	ns
tow	Output Active from End-of-Write <sup>(1)</sup>	0		0		0		ns
								2692 tbl 0
-				7142 Con	2X55 2X55 1'I & tary	7142 Con	X100 X100 n'l & itary	2692 tbl 0
Symbol	Parameter			7142 Con	2X55 1'l&	7142 Con	X100 n'I &	2692 tbl 0 Unit
		• 		7142 Con Mili	2X55 n'I & tary	7142 Con Mili	2X100 n'I & itary	
Symbol				7142 Con Mili	2X55 n'I & tary	7142 Con Mili	2X100 n'I & itary	
Symbol WRITE CYCL	E	•		7142 Con Mili Min.	2X55 n'I & tary	7142 Con Mili Min.	2X100 n'I & itary	Unit
Symbol MRITE CYCL twc	E Write Cycle Time <sup>(3)</sup>			7142 Con Mili Min.	2X55 tary Max.	7142 Con Mili Min.	X100 n'I & itary Max.	Unit
Symbol MRITE CYCL twc tew	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write			7142 Con Mili Min. 55 40	2X55 tary Max.	7142 Con Mili Min. 100 90	X100 n'I & itary Max.	Unit ns ns
Symbol MRITE CYCL twc tew taw	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write Address Valid to End-of-Write			7142 Con Mili Min. 55 40 40	2X55 tary Max.	7142 Con Mili Min. 100 90 90	X100 n'I & itary Max.	Unit ns ns
Symbol MRITE CYCLI twc tew taw tas	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time	•		7142 Con Mili Min. 55 40 40 0	2X55 tary Max.	7142 Con Mili Min. 100 90 90 0	X100 n'I & itary Max.	Unit ns ns ns ns
Symbol MRITE CYCL twc tew taw tas twp	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width <sup>(4)</sup>			7142 Con Mili Min. 555 40 40 0 30	2X55 tary Max.	7142 Con Mili Min. 100 90 90 0 55	X100 n'I & itary Max.	Unit ns ns ns ns ns
Symbol MRITE CYCL twc tew taw tas twp twr	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width <sup>(4)</sup> Write Recovery Time			7142 Con Mili Min. 55 40 40 40 0 30 0	2255 11 & tary Max. 	7142 Con Mili Min. 100 90 90 0 55 0	X100 n'I & Max. 	Unit ns ns ns ns ns ns
Symbol MRITE CYCLI twc tew taw tas twp twr twr twr	E Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write Address Valid to End-of-Write Address Set-up Time Write Pulse Width <sup>(4)</sup> Write Recovery Time Data Valid to End-of-Write			7142 Con Mili Min. 555 40 40 0 30 0 20	2255 1'l & Max. 	7142 Con Mili Min. 100 90 90 0 0 555 0 40	X100 n'I & tary Max.	Unit ns ns ns ns ns ns ns
Symbol VRITE CYCL twc tew taw tas twP twR twR twR twR	Write Cycle Time <sup>(3)</sup> Chip Enable to End-of-Write         Address Valid to End-of-Write         Address Set-up Time         Write Pulse Width <sup>(4)</sup> Write Recovery Time         Data Valid to End-of-Write         Output High-Z Time <sup>(1)</sup>			7142 Con Mili 555 40 40 40 0 30 0 20 	2X55 11 & tary Max. 	7142 Con Mili Min. 100 90 90 90 0 555 0 40 	X100 n'I & tary Max. 	Unit ns ns ns ns ns ns ns ns ns

2692 tbl 10

#### NOTES:

2. PLCC package only.

3. For Master/Slave combination, twc = tBAA + twP, since R/W = VIL must occur after tBAA.

4. If  $\overline{OE}$  is LOW during a R/ $\overline{W}$  controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If  $\overline{OE}$  is High during a R/ $\overline{W}$  controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

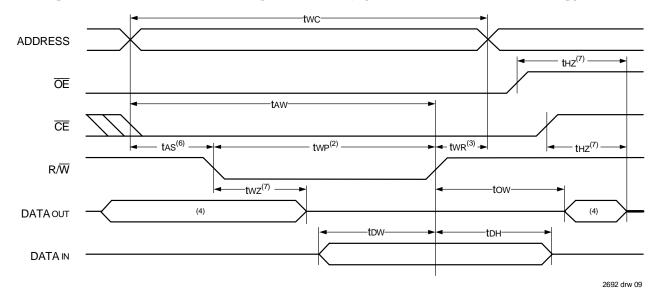
5. 'X' in part numbers indicates power rating (SA or LA).

6. Industrial temperature: for specific speeds, packages and powers contact your sales office.

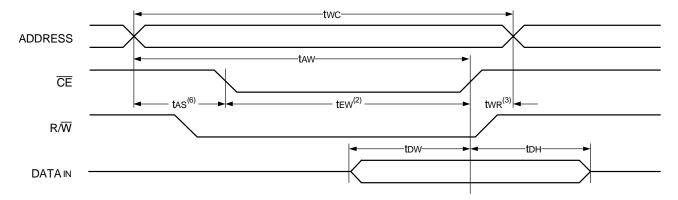
<sup>1.</sup> Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2). This parameter is guaranteed by device characterization but is not production tested.

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# Timing Waveform of Write Cycle No. 1, (R/W Controlled Timing)<sup>(1,5,8)</sup>



# Timing Waveform of Write Cycle No. 2, (CE Controlled Timing)<sup>(1,5)</sup>



- 1.  $R/\overline{W}$  or  $\overline{CE}$  must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of  $\overline{\text{CE}}$  = VIL and R/W = VIL.
- 3. twn is measured from the earlier of CE or R/W going HIGH to the end of the write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE LOW transition occurs simultaneously with or after the R/W LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal (CE or R/W) is asserted last.
- 7. This parameter is determined be device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If OE is LOW during a R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off data to be placed on the bus for the required tow. If OE is HIGH during a R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.

# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(7,8)</sup>

		7132X20 <sup>(1)</sup> 7142X20 <sup>(1)</sup> Com'l Only		7132X25 <sup>(2)</sup> 7142X25 <sup>(2)</sup> Com'l, Ind & Military		7132X35 7142X35 Com'l & Military		
Symbol	Parameter	Min.	Max.	Min. Max.		Min. Max.		Unit
BUSY Timing	g (For Master IDT7132 Only)		-		-	-	-	
<b>t</b> BAA	BUSY Access Time from Address		20		20	—	20	ns
tBDA	BUSY Disable Time from Address		20		20	—	20	ns
tBAC .	BUSY Access Time from Chip Enable		20	-	20		20	ns
tBDC	BUSY Disable Time from Chip Enable		20		20		20	ns
twdd	Write Pulse to Data Delay <sup>(2)</sup>		50		50	—	60	ns
twн	Write Hold After BUSY <sup>(6)</sup>	12		15		20	_	ns
tDDD	Write Data Valid to Read Data Delay <sup>(2)</sup>		35	-	35	_	35	ns
taps	Arbitration Priority Set-up Time <sup>(3)</sup>	5		5		5	—	ns
tBDD	BUSY Disable to Valid Data <sup>(4)</sup>		25		35		35	ns
BUSY Timing	g (For Slave IDT7142 Only)			•				
twв	Write to BUSY Input <sup>(5)</sup>	0		0		0	_	ns
twн	Write Hold After BUSY <sup>(6)</sup>	12		15		20	—	ns
twdd	Write Pulse to Data Delay <sup>(2)</sup>		40		50		60	ns
			1					
tDDD	Write Data Valid to Read Data Delay <sup>(2)</sup>		30		35		35	ns
tDDD	Write Data Valid to Read Data Delay <sup>(2)</sup>		30		35		35	ns 2692 tbl 11a
todd	Write Data Valid to Read Data Delay <sup>(2)</sup>		30	713 714 Con	35 2X55 2X55 n'l & itary	7142 Con	35 X100 X100 n'l & itary	
Symbol	Write Data Valid to Read Data Delay <sup>(2)</sup> Parameter		30	713 714 Con	2X55 2X55 n'l &	7142 Con	X100 X100 n'l &	
Symbol			30	713: 714; Con Mili	2X55 2X55 n'l & itary	7142 Con Mili	X100 X100 n'I & itary	2692 tbl 11:
Symbol	Parameter		30	713: 714; Con Mili	2X55 2X55 n'l & itary	7142 Con Mili	X100 X100 n'I & itary	2692 tbl 11:
Symbol BUSY Timing	Parameter g (For Master IDT7132 Only)		30	713; 714; Con Mili Min.	2X55 2X55 n'I & itary Max.	7142 Con Mili	X100 X100 n'I & itary Max.	2692 tbl 111
Symbol BUSY Timing	Parameter (For Master IDT7132 Only) BUSY Access Time from Address		30	713; 714; Con Mili Min.	2X55 2X55 n'I & itary Max. 30	7142 Con Mili Min.	X100 X100 n'I & itary Max. 50	2692 tbl 11: Unit
Symbol BUSY Timing tBAA tBDA	Parameter g (For Master IDT7132 Only) BUSY Access Time from Address BUSY Disable Time from Address		30	713; 714; Con Mili Min.	2X55 2X55 n'I & itary Max. 30 30	7142 Con Mili Min.	X100 X100 n'I & itary Max. 50 50	2692 tbl 11: Unit ns
Symbol BUSY Timing teaa teda teac	Parameter  (For Master IDT7132 Only)  BUSY Access Time from Address BUSY Disable Time from Address BUSY Access Time from Chip Enable		30	713; 714; Con Mili Min.	2X55 2X55 n'l & itary Max. 30 30 30	7142 Con Mili Min.	X100 X100 n'I & itary Max. 50 50 50	2692 tbl 111 Unit ns ns
Symbol BUSY Timing tBAA tBDA tBAC tBDC	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable		30	713; 714; Con Mili Min.	2X55 2X55 n'1 & ttary Max. 30 30 30 30	7142 Con Mili Min.	X100 X100 n'I & itary Max. 50 50 50 50	Unit ns ns ns ns
Symbol BUSY Timing tBAA tBDA tBAC tBDC tWDD	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup>		30	713: 714: Con Milii Min.	2X55 2X55 n'1 & ttary Max. 30 30 30 30	7142 Con Mili Min.	X100 X100 n'I & itary Max. 50 50 50 50	Unit Usit
Symbol BUSY Timing tBAA tBDA tBAC tBDC tWDD tWH	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup> Write Hold After BUSY <sup>(6)</sup>		30	713: 714: Con Milii Min.	2X55 2X55 n'i & itary Max. 30 30 30 30 30 30 	7142 Con Mili Min.	X100 X100 n'l & itary Max. 50 50 50 50 120 	Unit Unit ns ns ns ns ns ns ns
Symbol BUSY Timing tBAA tBDA tBAC tBDC tWDD tWH tDDD	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup> Write Hold After BUSY <sup>(6)</sup> Write Data Valid to Read Data Delay <sup>(2)</sup>		30	713: 714: Com Mili Min. — — — — 20 —	2X55 2X55 n'i & itary Max. 30 30 30 30 30 30 	7142 Com Mili Min. — — — — — 20 ——	X100 X100 n'l & itary Max. 50 50 50 50 120  100	Unit Unit ns ns ns ns ns ns ns ns
Symbol BUSY Timing teAA teDA teAC teDC twDD twH teDD twH teDD teDD	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup> Write Hold After BUSY <sup>6</sup> Write Data Valid to Read Data Delay <sup>(2)</sup> Arbitration Priority Set-up Time <sup>(3)</sup>		30	713: 714: Com Mili Min. — — — — 20 —	2X55 2X55 n'i & itary Max. 30 30 30 30 30 30 55 55 	7142 Com Mili Min. — — — — — 20 ——	X100 X100 n'l & itary Max. 50 50 50 50 50 120  100 	Unit Unit ns ns ns ns ns ns ns ns ns ns
Symbol BUSY Timing teAA teDA teAC teDC twDD twH teDD twH teDD teDD	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup> Write Hold After BUSY <sup>(6)</sup> Write Data Valid to Read Data Delay <sup>(2)</sup> Arbitration Priority Set-up Time <sup>(3)</sup> BUSY Disable to Valid Data <sup>(4)</sup>		30	713: 714: Com Mili Min. — — — — 20 —	2X55 2X55 n'i & itary Max. 30 30 30 30 30 30 55 55 	7142 Com Mili Min. — — — — — 20 ——	X100 X100 n'l & itary Max. 50 50 50 50 50 120  100 	Unit Unit ns ns ns ns ns ns ns ns ns ns
Symbol BUSY Timing tBAA tBDA tBDA tEDC tWDD tWH tDDD tWH tDDD tWH tDDD tBDD <b>BUSY Timing</b>	Parameter         g (For Master IDT7132 Only)         BUSY Access Time from Address         BUSY Disable Time from Address         BUSY Access Time from Address         BUSY Access Time from Chip Enable         BUSY Disable Time from Chip Enable         Write Pulse to Data Delay <sup>(2)</sup> Write Hold After BUSY <sup>(6)</sup> Write Data Valid to Read Data Delay <sup>(2)</sup> Arbitration Priority Set-up Time <sup>(3)</sup> BUSY Disable to Valid Data <sup>(4)</sup> g (For Slave IDT7142 Only)		30	713: 714: Com Mili Min. 	2X55 2X55 n'1 & tary Max. 30 30 30 30 30 30 55 55 50	7142 Com Mili Min. 	X100 X100 n'l & tary Max. 50 50 50 50 50 120  100  65	Unit Unit NS NS NS NS NS NS NS NS NS
Symbol BUSY Timing tBAA tBDA tBAC tBDC tWDD tWH tDDD tWH tDDD tAPS tBDD BUSY Timing tWB	Parameter         g (For Master IDT7132 Only)         BUSY       BUSY Access Time from Address         BUSY       Disable Time from Address         BUSY       Disable Time from Chip Enable         BUSY       Disable Time from Chip Enable         Write       Pulse to Data Delay <sup>(2)</sup> Write       Hold After BUSY <sup>(6)</sup> Write Data Valid to Read Data Delay <sup>(2)</sup> Arbitration Priority Set-up Time <sup>(3)</sup> BUSY       Disable to Valid Data <sup>(4)</sup> g (For Slave IDT7142 Only)         Write to BUSY Input <sup>(6)</sup>		30	713: 714: Com Mili Min. — — — — 20 — 20 — 5 5 — 0	2X55 2X55 n'1 & tary Max. 30 30 30 30 30 30 30 55 50 50	7142 Com Mili Min. 	X100 X100 n'l & itary Max. 50 50 50 50 120  65	Unit Unit NS NS NS NS NS NS NS NS NS NS

NOTES:

1. PLCC package only.

2. Port-to-port delay through RAM cells from the writing port to the reading port, refer to "Timing Waveform of Write with Port -to-Port Read and BUSY."

3. To ensure that the earlier of the two ports wins.

4. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual) or tDDD - tDw (actual).

5. To ensure that a write cycle is inhibited on port "B" during contention on port "A".

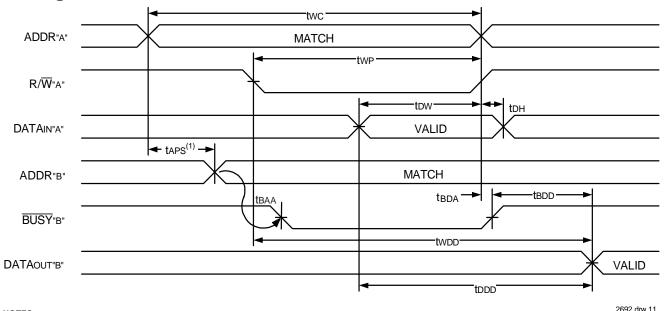
6. To ensure that a write cycle is completed on port "B" after contention on port "A".

7. 'X' in part numbers indicates power rating (SA or LA).

8. Industrial temperature: for specific speeds, packages and powers contact your sales office.

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# Timing Waveform of Write with Port-to-Port Read and BUSY<sup>(2,3,4)</sup>



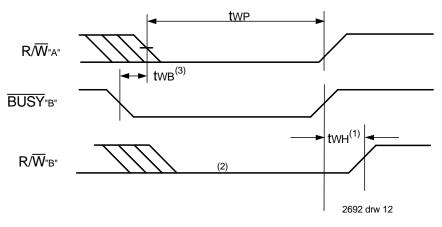
#### NOTES:

1. To ensure that the earlier of the two ports wins. tAPS is ignored for Slave (IDT7142).

- 2.  $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$
- 3.  $\overline{OE}$  = VIL for the reading port.

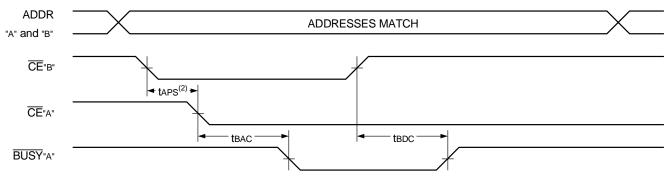
4. All timing is the same for the left and right ports. Port "A" may be either the left or right port. Port "B" is opposite from port "A".

# Timing Waveform of Write with $\overline{\text{BUSY}}^{(4)}$



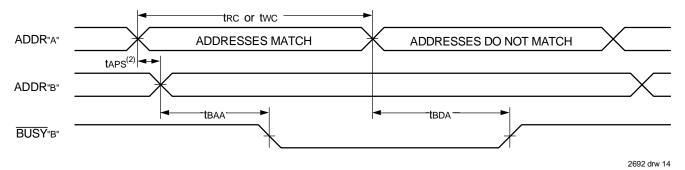
- 1. twn must be met for both BUSY Input (IDT7142, slave) or Output (IDT7132, master).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb applies only to the slave version (IDT7142).
- 4. All timing is the same for the left and right ports. Port 'A' may be either the left or right port. Port "B" is opposite from port "A".

# Timing Waveform of $\overline{\text{BUSY}}$ Arbitration Controlled by $\overline{\text{CE}}$ Timing<sup>(1)</sup>



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# Timing Waveform of $\overline{\text{BUSY}}$ Arbitration Controlled by Address Match Timing<sup>(1)</sup>



#### NOTES:

1. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

2. If tAPS is not satisified, the BUSY will be asserted on one side or the other, but there is no guarantee on which side BUSY will be asserted (7132 only).

# **Truth Tables**

### Table I. Non-Contention Read/Write Control<sup>(4)</sup>

Left or Right Port <sup>(1)</sup>			ort <sup>(1)</sup>	
R/W	ĒĒ	ŌĒ	D0-7	Function
Х	Н	Х	Z	Port Disabled and in Power-Down Mode, ISB2 or ISB4
Х	Н	Х	Z	CER = CEL = VH, Power-Down Mode, ISB1 or ISB3
L	L	Х	DATAIN	Data on Port Written into Memory <sup>2)</sup>
Н	L	L	DATAOUT	Data in Memory Output on Port <sup>(3)</sup>
Х	L	Н	Z	High Impedance Outputs

#### NOTES:

1. AoL - A10L  $\neq$  AOR - A10R

2. If  $\overline{\text{BUSY}}$  = L, data is not written.

3. If <u>BUSY</u> = L, data may not be valid, see twDD and tDDD timing.

4. 'H' = VIH, 'L' = VIL, 'X' = DON'T CARE, 'Z' = HIGH IMPEDANCE

# Table II — Address BUSY Arbitration

Inputs			Out	puts	
ĊĒ∟	ĊĒr	AOL-A10L AOR-A10R	BUS YL <sup>(1)</sup>	BUSTR <sup>(1)</sup>	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

#### NOTES:

 Pins BUSYL and BUSYR are both outputs for IDT7132 (master). Both are inputs for IDT7142 (slave). BUSYX outputs on the IDT7132 are open drain, not push-pull outputs. On slaves the BUSYX input internally inhibits writes.

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- 'L' if the inputs to the opposite port were stable prior to the address and enable inputs of this port. 'H' if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

# **Functional Description**

The IDT7132/IDT7142 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7132/IDT7142 has an automatic power down feature controlled by  $\overline{CE}$ . The  $\overline{CE}$  controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{CE} = VIH$ ). When a port is enabled, access to the entire memory array is permitted.

### **Busy Logic**

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a busy indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{\text{BUSY}}$  Logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{\text{BUSY}}$  outputs together and use any  $\overline{\text{BUSY}}$  indication as an interrupt source to flag the event of an illegal or illogical operation.

#### Military, Industrial and Commercial Temperature Ranges

The BUSY outputs on the IDT7132 RAM master are totem-pole type outputs and do not require pull-up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array does not require the use of an external AND gate.

### Width Expansion with Busy Logic Master/Slave Arrays

When expanding an SRAM array in width while using BUSY logic, one master part is used to decide which side of the SRAM array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the BUSY signal as a write inhibit signal. Thus on the IDT7132/IDT7142 SRAMs the BUSY pin is an output if the part is Aster (IDT7142), and the BUSY pin is an input if the part is a Slave (IDT7142) as shown in Figure 3.

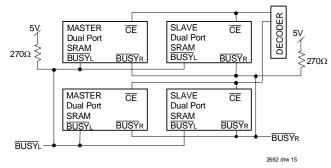
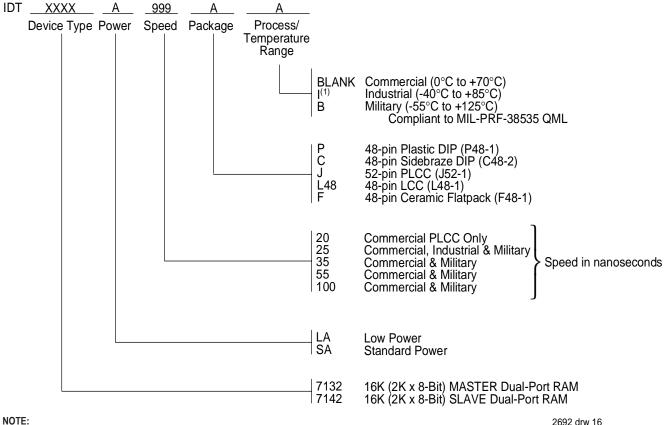


Figure 4. Busy and chip enable routing for both width and depth expansion with IDT7132 (Master) and (Slave) IDT7142 SRAMs.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating  $\overline{\text{BUSY}}$  on one side of the array and another master indicating  $\overline{\text{BUSY}}$  on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a Master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with either the R/W signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

### **Ordering Information**



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- 1. Industrial temperature range is available.
  - For specific speeds, packages and powers contact your sales office.

### **Datasheet Document History**

03/24/99:	Initiated datasheet document history				
	Converted to new format				
	Cosmetic and typographical corrections				
	Pages 2 and 3 Added additional notes to pin configurations				
06/08/99:	Changed drawing format				
08/26/99:	Page 14 Changed Busy Logic and Width Expansion copy				
11/10/99:	Replaced IDT logo				
01/12/00:	Pages 1 and 2 Moved full "Description" to page 2 and adjusted page layouts				
	Page 1 Added "(LAonly)" to paragraph				
	Page 2 Fixed P48-1 body package description				
	Page 3 Increased storage temperature parameters				
	Clarified TA parameter				
	Page 4 DC Electrical parameters-changed wording from "open" to "disabled"				
	Page 6 Added asteriks to Figures 1 and 3 in drw 06				
	Page 14 Corrected part numbers				
	Changed ±500mV to 0mV in notes				
	Datasheet Document History continued on page 16				
	Datasheet Document history continued of page 10				

Military, Industrial and Commercial Temperature Ranges

# **Datasheet Document History (cont'd)**

06/11/04: Page 6Corrected errors in Figure 3 by changing 1250Ω to 270Ω and removing "or Int" and Int<br/>Page 4, 7, 9, 11 & 15<br/>Clarified Industrial temp offering for 25ns<br/>Page 5<br/>Removed INT from VoL parameter in DC Electrical Characteristics table<br/>Page 6 Updated AC Test Conditions Input Rise/Fall Times from 5ns to 3ns



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